

IGBT MODULE (N series)

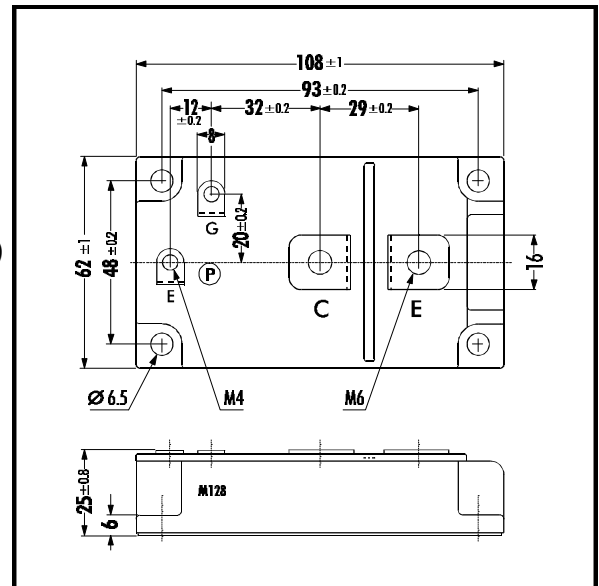
■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (~3 Times Rated Current)

■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

■ Outline Drawing



■ Maximum Ratings and Characteristics

• Absolute Maximum Ratings (T_c=25°C)

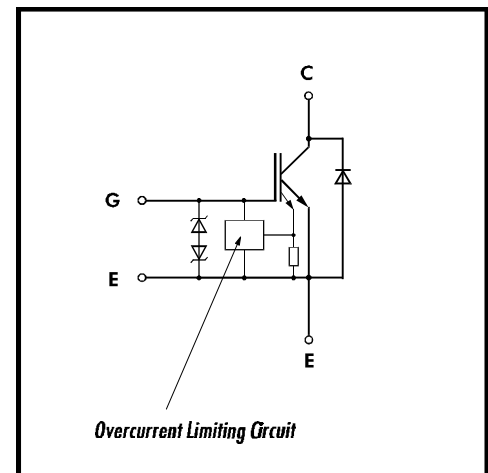
Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V _{CES}	600	V
Gate -Emitter Voltage	V _{GES}	± 20	V
Collector Current	I _C	600	A
	I _C PULSE	1200	
	-I _C	600	
	-I _C PULSE	1200	
Max. Power Dissipation	P _C	2000	W
Operating Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Isolation Voltage	V _{is}	2500	V
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	4.5	
	Terminals *3	1.7	

Note: *1:Recommendable Value; 2.5 ~ 3.5 Nm (M5) or (M6)

*2:Recommendable Value; 3.5 ~ 4.5 Nm (M6)

*3:Recommendable Value; 1.3 ~ 1.7 Nm (M4)

■ Equivalent Circuit



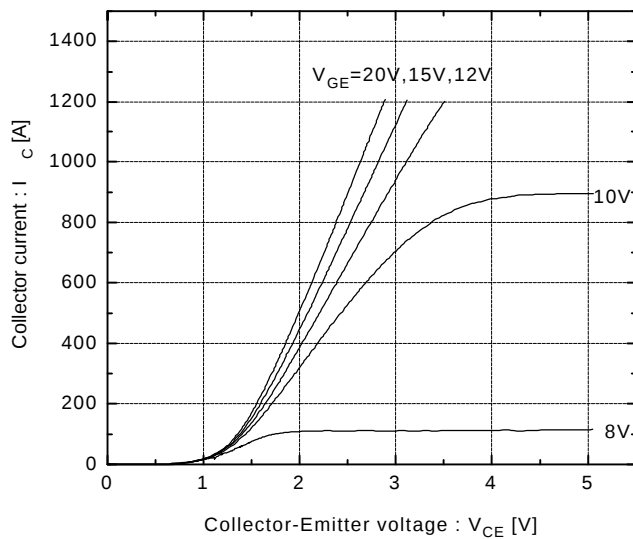
• Electrical Characteristics (at T_J=25°C)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =600V			4.0	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} =0V V _{GE} =± 20V			60	μA
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{GE} =20V I _C =600mA	4.5		7.5	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _C =600A			2.8	V
Input capacitance	C _{ies}	V _{GE} =0V		39600		pF
Output capacitance	C _{oes}	V _{CE} =10V		8800		
Reverse Transfer capacitance	C _{res}	f=1MHz		4000		
Turn-on Time	t _{ON}	V _{CC} =300V		0.6	1.2	μs
	t _r	I _C =600A		0.2	0.6	
Turn-off Time	t _{OFF}	V _{GE} =± 15V		0.6	1.0	
	t _f	R _G =2.7Ω		0.2	0.35	
Diode Forward On-Voltage	V _F	I _F =600A V _{GE} =0V			3.0	V
Reverse Recovery Time	t _{rr}	I _F =600A			300	ns

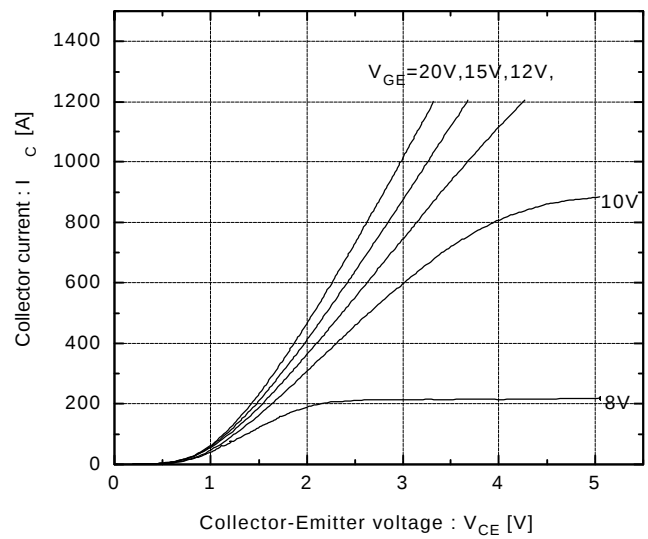
• Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R _{th(j-c)}	IGBT			0.063	°C/W
	R _{th(j-e)}	Diode			0.11	
	R _{th(c-f)}	With Thermal Compound		0.0125		

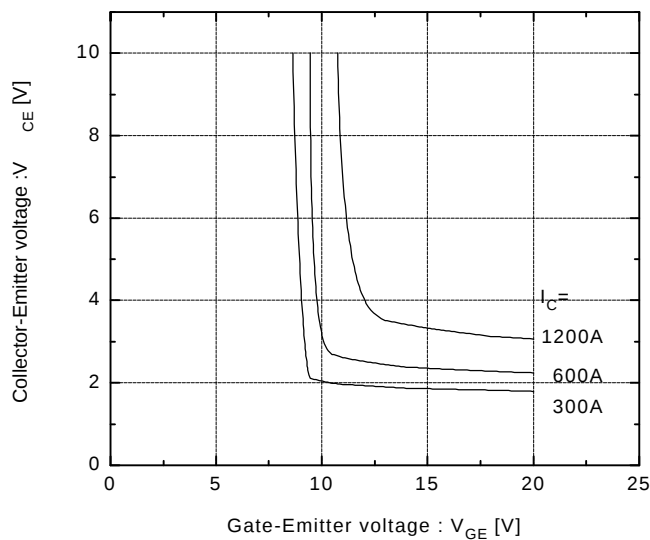
Collector current vs. Collector-Emittor voltage

 $T_J = 25^\circ\text{C}$


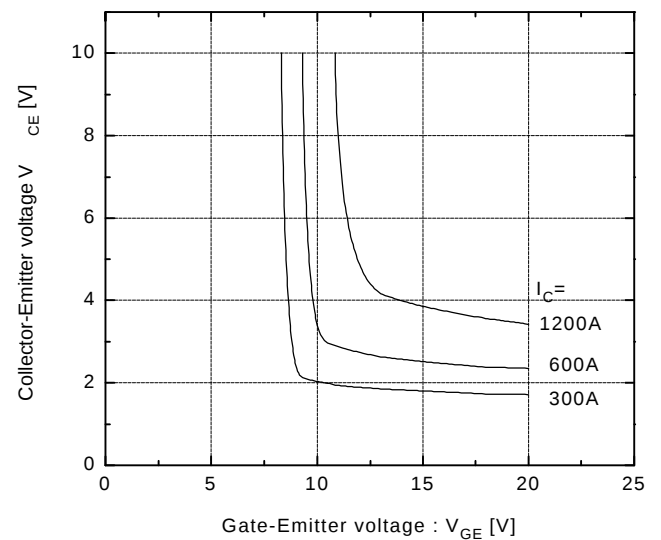
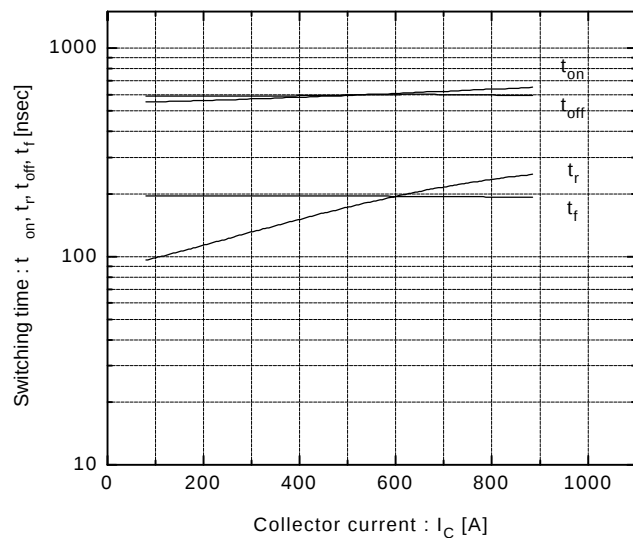
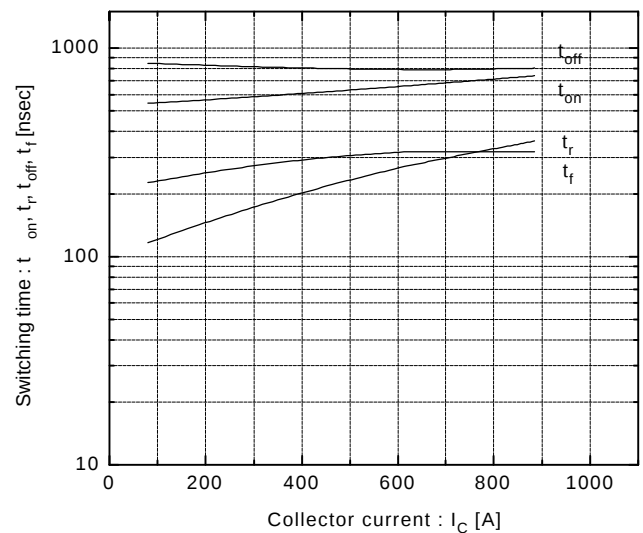
Collector current vs. Collector-Emittor voltage

 $T_J = 125^\circ\text{C}$


Collector-Emittor vs. Gate-Emittor voltage

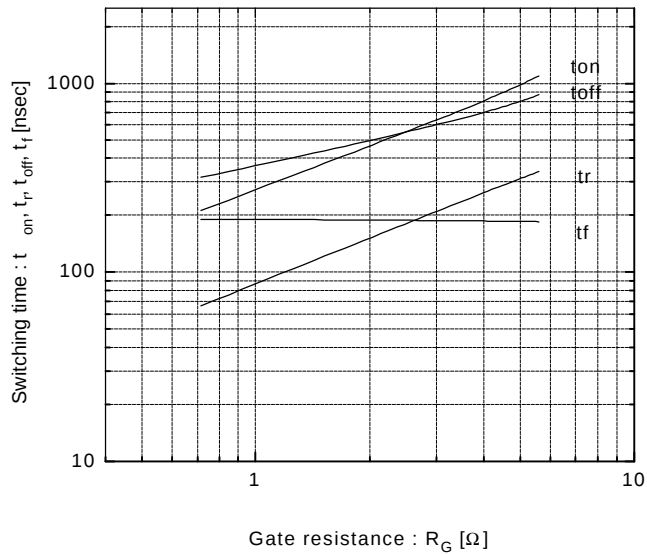
 $T_J = 25^\circ\text{C}$


Collector-Emittor vs. Gate-Emittor voltage

 $T_J = 125^\circ\text{C}$

 Switching time vs. Collector current
 $V_{CC} = 300V, R_G = 2.7\Omega, V_{GE} = \pm 15V, T_J = 25^\circ\text{C}$

 Switching time vs. Collector current
 $V_{CC} = 300V, R_G = 2.7\Omega, V_{GE} = \pm 15V, T_J = 125^\circ\text{C}$


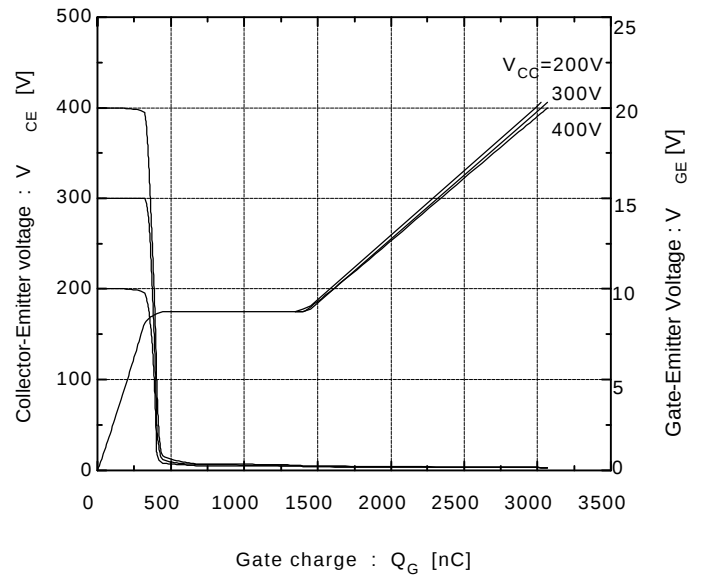
Switching time vs. R_G

$V_{CC}=300V$, $I_C=600A$, $V_{GE}=\pm 15V$, $T_J=25^\circ C$



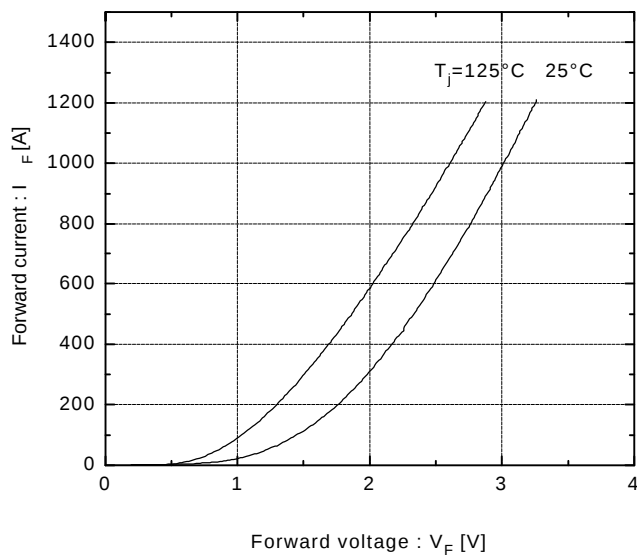
Dynamic input characteristics

$T_J=25^\circ C$



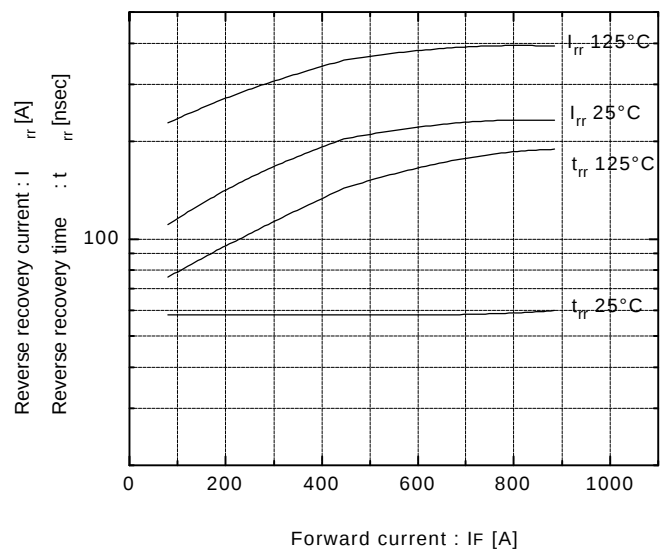
Forward current vs. Forward voltage

$V_{GE}=0V$

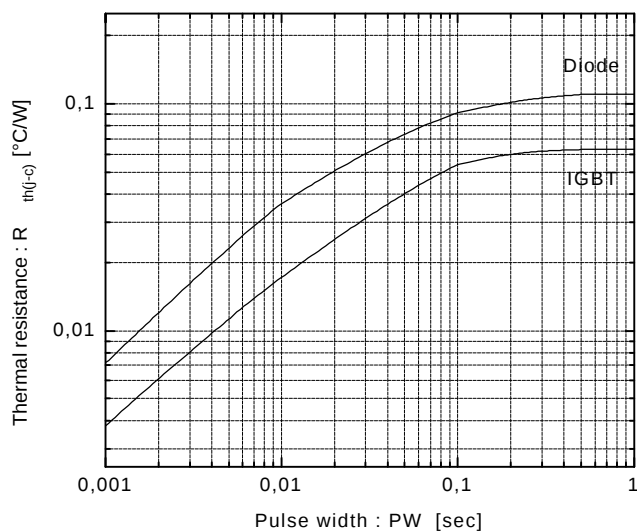


Reverse recovery characteristics

t_{rr} , I_{rr} vs. I_F

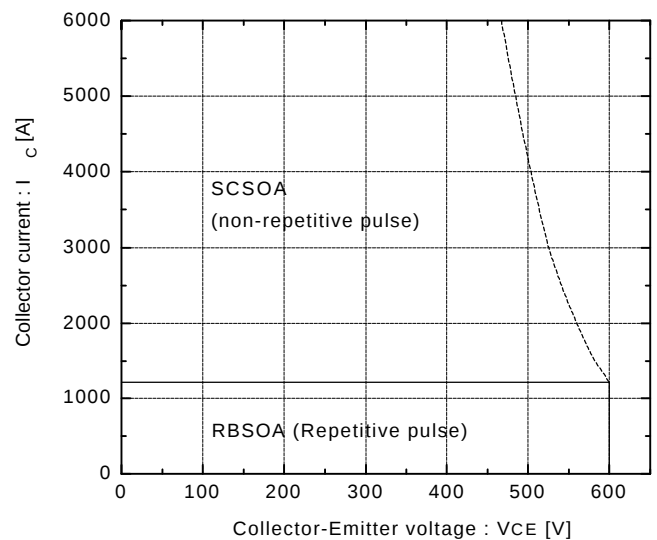


Transient thermal resistance

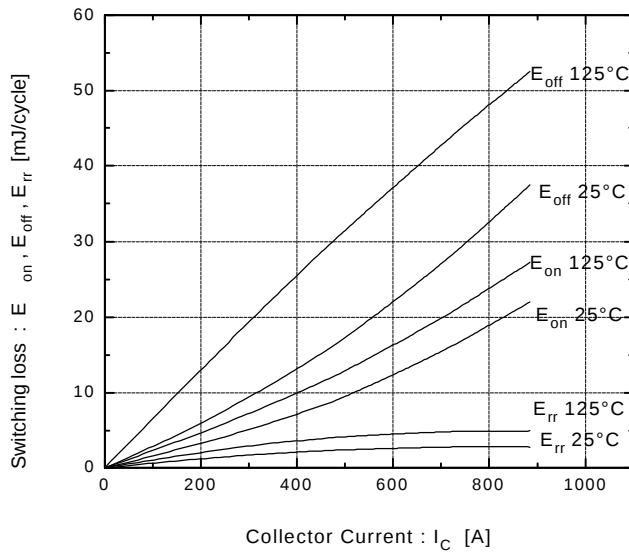


Reversed biased safe operating area

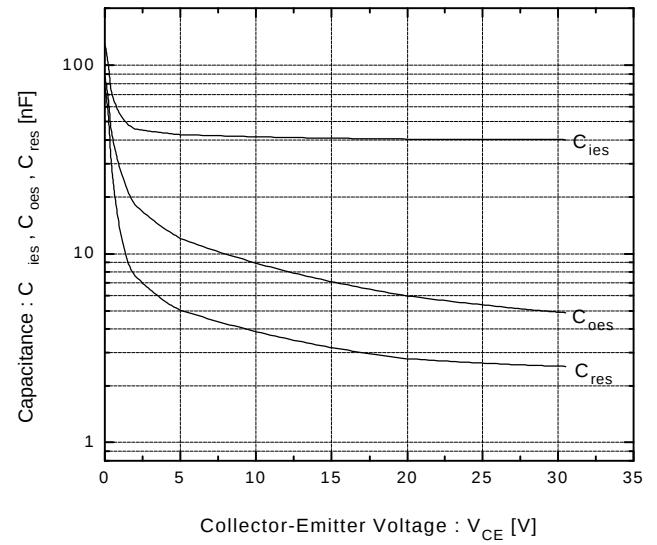
$+V_{GE}=15V$, $-V_{GE}\leq 15V$, $T_J\leq 125^\circ C$, $R_G\geq 2.7\Omega$



Switching loss vs. Collector current

 $V_{CC}=300V$, $R_G=2.7\Omega$, $V_{GE}=\pm 15V$ 

Capacitance vs. Collector-Emitter voltage

 $T_J=25^\circ C$ **Fuji Electric GmbH**

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